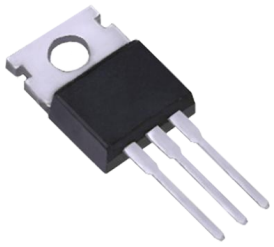
10A, 900V N-CHANNEL POWER MOSFET

■ DESCRIPTION

The UTC**10N90** is a N-channel mode power MOSFET using UTC's advanced technology to provide costumers with planar stripe and DMOS technology. This technology allows a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **10N90** is generally applied in high efficiency switch mode power supply.



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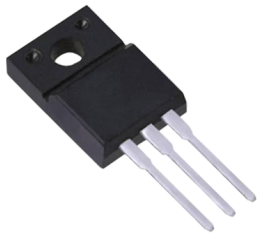
■ FEATURES

* $R_{DS(ON)}$ =1.35Ω@V_{GS} =10V
* Lower Leakage Current: 25μA (Max.) @ V_{DS} = 900V
* Improved Gate Charge



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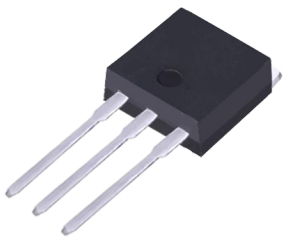

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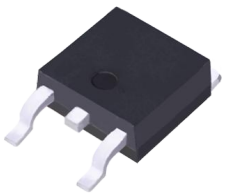

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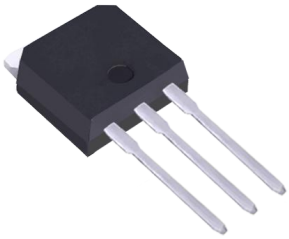

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■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	900	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	10	A
	Pulsed (Note 2)	I_{DM}	40	A
Avalanche Current (Note 2)		I_{AR}	10	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	794	mJ
	Repetitive (Note 2)	E_{AR}	28	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	1.5	V/ns
Power Dissipation		P_D	183	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55~+150	°C

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. L = 15mH, I_{AS} = 10A, V_{DD} = 50V, R_G = 27Ω, Starting T_J = 25°C
3. I_{SD} ≤ 10A, di/dt ≤ 190A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test: Pulse width ≤ 250μs, Duty cycle ≤ 2%

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	40	°C/W
Junction to Case	θ_{JC}	0.68	°C/W

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	900			V
Breakdown Voltage Temperature Coefficient		$\triangle BV_{DSS}/\triangle T_J$	I_D=250μ		1.11		V/°C
Drain-Source Leakage Current		I_{DSS}	V_{DS}=900V			25	μA
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=+30V			100	nA
	Reverse		V_{GS}=-30V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{GS}=V_{DS}, I_D=250μA	3.0		5.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=5A		1.15	1.35	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		2760	3580	pF
Output Capacitance		C_{OSS}			245	290	pF
Reverse Transfer Capacitance		C_{RSS}			105	125	pF

■ ELECTRICAL CHARACTERISTICS(Cont.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	V_{GS}=10V, V_{DS}=720V, I_D=10A (Note 1, 2)		127	165	nC
Gate to Source Charge	Q_{GS}			19.2		nC
Gate to Drain Charge	Q_{GD}			56.8		nC
Turn-ON Delay Time	$t_{D(ON)}$	V_{DD}=450V, I_D=10A, R_G=9.6Ω (Note 1, 2)		29	70	ns
Rise Time	t_R			54	20	ns
Turn-OFF Delay Time	$t_{D(OFF)}$			161	330	ns
Fall-Time	t_F			47	105	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S	Integral Reverse Pn-Diode In The MOSFET			10	A
Maximum Body-Diode Pulsed Current (Note1)	I_{SM}				40	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	I_S=10A, V_{GS}=0V, T_J=25°C			1.4	V
Body Diode Reverse Recovery Time	t_{rr}	I_F=10A, dI_F/dt=100A/μs, T_J=25°C (Note 1)		690		ns
Body Diode Reverse Recovery Charge	Q_{RR}			11.94		μC

Note: 1. Pulse Test: Pulse width ≤ 250μs, Duty cycle ≤ 2%
2. Essentially independent of operating temperature

■ TYPICAL CHARACTERISTICS